

08-01-05

IFW

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Sei-Hyung Ryu
Serial No.: 10/698,170
Filed: October 30, 2003
Group Art Unit: 2818
Confirmation No. 2502
Examiner: Long K. Tran

For: VERTICAL JFET LIMITED SILICON CARBIDE POWER METAL-OXIDE

SEMICONDUCTOR FIELD EFFECT TRANSISTORS (AS AMENDED)

Date: July 29, 2005

MAIL STOP AMENDMENT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

AMENDMENT AND RESPONSE TO RESTRICTION REQUIREMENT

Sir:

Applicant provides the present Amendment to address the issues raised in the Office Action mailed July 12, 2005.

If any extension of time for the accompanying Amendment and Response is required, Applicants request that this be considered a petition therefore. The Commissioner is hereby authorized to charge any additional fee, which may be required, or credit any refund, to Deposit Account No. 50-0220.

Amendments to the Title begin on page 2 of this paper.

Amendments to the Claims begin on page 3 of this paper.

Remarks/Arguments begin on page 9 of this paper.

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Amendments to the Title:

Please replace the title with the following amended title:

VERTICAL JFET LIMITED SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS AND METHODS OF FABRICATING VERTICAL JFET SILICON CARBIDE METAL-OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTORS